

N-CHANNEL POWER MOSFET MEM4N65

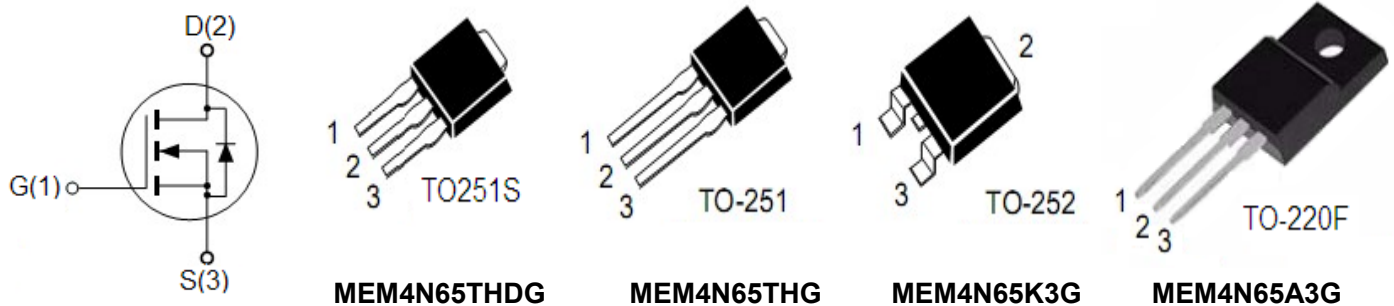
General Description

The MEM4N65 is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

Features

- 650V, 4A
- $R_{DS(ON)}=2.1\Omega@V_{GS}=10V$
- LOW CRSS
- FAST SWITCHING
- PACKAGE :TO251,TO251S,TO252,TO-220F

Pin Configuration



Maximum Ratings($T_A=25^\circ C$)

Parameter		Symbol	Ratings		Unit
Drain-Source Voltage		V_{DSS}	650V		V
Gate-Source Voltage		V_{GSS}	± 30		V
Drain Current	$T_A=25^\circ C$	I_D	4		A
	$T_A=100^\circ C$		2.5		
Pulsed Drain Current(Note1、2)		I_{DM}	16		A
Avalanche Energy	Single Pulsed(Note1)	E_{AS}	240		mJ
	Repetitive (Note2)	E_{AR}	10.6		
Total Power Dissipation	$T_A=25^\circ C$	P_d	TO-251	50	W
			TO-220F	33	
			TO-252	57	
Operating Temperature Range		T_{Opr}	-55-150		$^\circ C$
Storage Temperature Range		T_{stg}	-55-150		$^\circ C$